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Docket No.: SON-2628
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:

Confirmation No.: 1800

Shinji OMORI et al.

Patent No.: 7,109,500

Issued: September 19, 2006

For: MASK PATTERN CORRECTION METHOD,
PRODUCTION METHOD OF SEMICONDUCTOR
DEVICE, MASK PRODUCTION METHOD AND
MASK

REQUEST FOR CERTIFICATE OF CORRECTION

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

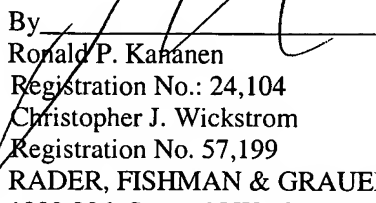
Certificate
APR 24 2007
of Correction

It is respectfully requested that a Certificate of Correction be issued in connection with the above-identified patent. It appears that mistakes were recorded through the fault of the Patent and Trademark Office in the printing of the patent as clearly disclosed by the records of the Office within the meaning of 35 USC § 254. Accordingly, two copies of the special Certificate of Correction are attached hereto. It is believed that the error noted is an error of consequence involving the title of the invention and thus warrants the granting of a Certificate of Correction. Copies of the first page of the application showing the correct title, the declaration showing the correct title, and the Official Filing Receipt with the correct title are enclosed for the convenience of the PTO. It is believed that the error was made on the part of the PTO and that no government fee is required.

Should any costs be incurred, please consider this authorization to charge Deposit Account No. 18-0013.

Dated: April 20, 2007

Respectfully submitted,

By 
Ronald P. Kananen
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APR 24 2007

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,109,500

DATED : September 19, 2006

INVENTOR(S): Shinji OMORI et al

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page:

Item (54) should be read as follows:

-- MASK PATTERN CORRECTION METHOD, PRODUCTION METHOD OF SEMICONDUCTOR DEVICE, MASK PRODUCTION METHOD AND MASK--.

MAILING ADDRESS OF SENDER:

Customer No. 23353
Rader, Fishman & Grauer PLLC
1233 20th Street, NW
Suite 501
Washington, DC 20036

PATENT NO. 7,109,500

APR 24 2007



Docket No.: SON-2628

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of:

Shinji OMORI, et al.

Application No.: 10/509,230

Filing Date: September 24, 2003

For: MASK PATTERN CORRECTION
METHOD, PRODUCTION METHOD OF
SEMICONDUCTOR DEVICE, MASK
PRODUCTION METHOD AND MASK

Group Art Unit: 2812

Confirmation No.: 1800

REQUEST FOR CORRECTED FILING RECEIPT

Attention: Fax: 703-746-9195
Office of Initial Patent Examination's
Filing Receipt Correction

Commissioner for Patents
P.O. Box 1450
Washington, D.C. 22313-1450

Sir:

1. Attached is a copy of the official filing receipt received from the PTO in the above application for which issuance of a corrected filing receipt is respectfully requested.
2. There is an error with respect to the following, which is incorrectly entered. We are also enclosing a copy of the executed declaration showing the correct data.

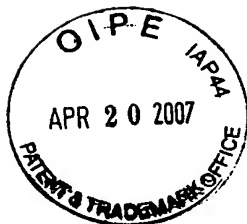
Error:

TITLE

Correct data to title:

Mask pattern correction method, production method
of semiconductor device, mask production method
and mask

APR 24 2007.



UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/509,230	09/24/2004	2812	1200	SON-2628	24	26	5

CONFIRMATION NO. 1800

23353
RADER FISHMAN & GRAUER PLLC
LION BUILDING
1233 20TH STREET N.W., SUITE 501
WASHINGTON, DC 20036

FILING RECEIPT



OC000000015145335

Date Mailed: 02/14/2005

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. **If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).**

Applicant(s)

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Assignment For Published Patent Application

Sony Corp., Tokyo, JAPAN

Power of Attorney:

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Domestic Priority data as claimed by applicant

This application is a 371 of PCT/JP03/03455 03/20/2003

Foreign Applications

JAPAN 2002-92612 03/28/2002

Projected Publication Date: 05/19/2005

Non-Publication Request: No

APR 24 2007

Early Publication Request: No

Title

Mask pattern correction method, semiconductor device manufacturing method, mask manufacturing method and mask

production method of

Preliminary Class

438

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Title 35, United States Code, Section 184
Title 37, Code of Federal Regulations, 5.11 & 5.15**

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PR 2 4 2007



DESCRIPTION

MASK PATTERN CORRECTION METHOD, PRODUCTION METHOD OF
SEMICONDUCTOR DEVICE, MASK PRODUCTION METHOD AND MASK

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TECHNICAL FIELD

The present invention relates to a mask pattern
correction method of a mask used in a lithography step, a
production method of a semiconductor device, a mask
10 production method and a mask, particularly relates to a
mask pattern correction method capable of preventing
positional deviation of a pattern by the mask deformation
due to gravity.

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BACKGROUND ART

As an exposure technique of the next generation to
take over photolithography, transfer type exposure
methods using charged particles, such as an electron beam
and an ion beam, have been developed. A mask having a
20 thin film region (membrane) is used in common in the new
techniques. A thickness of a membrane on the mask surface
side is 100 nm to 10 μ m or so, and a transfer pattern is
arranged on the membrane. The membrane is formed, for
example, by partially performing etching on a mask
25 material including a silicon wafer from the mask back

APR 24 2007



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PTO/SB/01 (3-97)

Approved for use through 6/30/98. OMB 0651-0032

Patent and Trademark Office; US DEPARTMENT OF COMMERCE

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**DECLARATION FOR
UTILITY OR DESIGN
PATENT APPLICATION**☐ Declaration
submitted with or
initial filing☐ Declaration
submitted after
initial filing

Attorney Docket No.

First Named Inventor

COMPLETE IF KNOWN

Application No.

Filing Date

Group Art Unit

Examiner Name

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (only if one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

MASK PATTERN CORRECTION METHOD, PRODUCTION METHOD OF
SEMICONDUCTOR DEVICE, MASK PRODUCTION METHOD AND MASK

(Title of the Invention)

the specification of which

☐ is attached hereto
or☐ was filed on 03/20/2003 United States Application Number or PCT International Application Number:
PCT/JP03/ and was amended on _____ (if applicable).
03455

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment specifically referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code § 119 (a)-(d) of any foreign application(s) for patent or inventor's certificate, or § 365(a) of any PCT international application which designated at least one country other than the United States of America, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or of any PCT international application having a filing date before that of the application on which priority is claimed.

Prior Foreign Application Number(s)	Country	Foreign Filing Date (MM/DD/YY)	Priority Not Claimed	Certified Copy Attached	
				YES	NO
2002-092612	JP	03/28/2002		<input type="checkbox"/>	<input type="checkbox"/>
PCT/JP03/03455	WO	03/20/2003		<input type="checkbox"/>	<input type="checkbox"/>
				<input type="checkbox"/>	<input type="checkbox"/>
				<input type="checkbox"/>	<input type="checkbox"/>

☐ Additional foreign application numbers are listed on a supplemental priority data sheet PTO/SB/02B attached hereto:

I hereby claim the benefit under Title 35, United States Code § 119(e) of any United States provisional application(s) listed below.

Application Number (s)	Filing Date (MM/DD/YY)	<input type="checkbox"/> Additional provisional application numbers are listed on a supplemental priority data sheet PTO/SB/02B attached hereto.

APR 24 2007